

# Silicon Carbide (SiC) MOSFET - EliteSiC, 44 mohm, 650 V, M2, TOLL NTBL060N065SC1

## Features

- Typ.  $R_{DS(on)} = 44 \text{ m}\Omega @ V_{GS} = 18 \text{ V}$   
Typ.  $R_{DS(on)} = 60 \text{ m}\Omega @ V_{GS} = 15 \text{ V}$
- Ultra Low Gate Charge ( $Q_{G(tot)} = 74 \text{ nC}$ )
- High Speed Switching with Low Capacitance ( $C_{oss} = 133 \text{ pF}$ )
- 100% Avalanche Tested
- $T_J = 175^\circ\text{C}$
- RoHS Compliant

## Typical Applications

- SMPS (Switching Mode Power Supplies)
- Solar Inverters
- UPS (Uninterruptable Power Supplies)
- Energy Storages

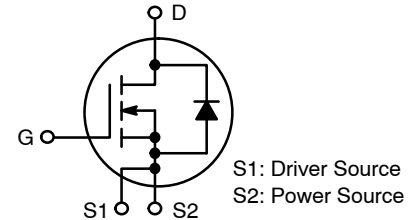
## MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	650	V	
Gate-to-Source Voltage		$V_{GS}$	-8/+22.6	V	
Recommended Operation Values of Gate-to-Source Voltage		$T_C < 175^\circ\text{C}$ $V_{GSop}$	-5/+18	V	
Continuous Drain Current (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$	46	A
			$P_D$	170	W
Continuous Drain Current (Note 1)	Steady State	$T_C = 100^\circ\text{C}$	$I_D$	33	A
			$P_D$	85	W
Pulsed Drain Current (Note 2)	$T_C = 25^\circ\text{C}$		$I_{DM}$	115	A
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		$I_S$	46	A	
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 10.1 \text{ A}$ , $L = 1 \text{ mH}$ ) (Note 3)		$E_{AS}$	51	mJ	
Maximum Lead Temperature for Soldering (1/8" from case for 5 s)		$T_L$	260	$^\circ\text{C}$	

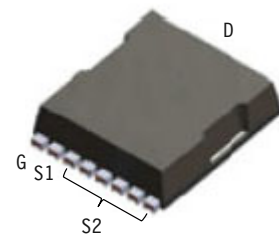
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. EAS of 51 mJ is based on starting  $T_J = 25^\circ\text{C}$ ;  $L = 1 \text{ mH}$ ,  $I_{AS} = 10.1 \text{ A}$ ,  $V_{DD} = 50 \text{ V}$ ,  $V_{GS} = 18 \text{ V}$ .

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
650 V	70 m $\Omega$ @ 18 V	46 A

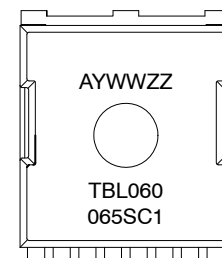


N-Channel MOSFET



H-PSOF8L  
CASE 100DC

## MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code
- TBL060065SC1 = Specific Device Code

## ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

# NTBL060N065SC1

## THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	0.88	°C/W
Junction-to-Ambient – Steady State (Note 1, 4)	$R_{\theta JA}$	43	

4. Device on 1 in<sup>2</sup>, 2 oz copper pad on 1.5 × 1.5 in. board of FR-4 material.

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 V, I_D = 1 mA$	650			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 20 mA$ , refer to 25°C		0.15		V/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0 V$ $V_{DS} = 650 V$	$T_J = 25^\circ C$		10	μA
			$T_J = 175^\circ C$		1	mA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = +18/-5 V, V_{DS} = 0 V$			250	nA

### ON CHARACTERISTICS

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 6.5 mA$	1.8	2.8	4.3	V
Recommended Gate Voltage	$V_{GOP}$		-5		+18	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 15 V, I_D = 20 A, T_J = 25^\circ C$ $V_{GS} = 18 V, I_D = 20 A, T_J = 25^\circ C$ $V_{GS} = 18 V, I_D = 20 A, T_J = 175^\circ C$		60		mΩ
				44	70	
				50		
Forward Transconductance	$g_{FS}$	$V_{DS} = 10 V, I_D = 20 A$ (Note 5)		12		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0 V, f = 1 MHz,$ $V_{DS} = 325 V$ (Note 5)		1473		pF
Output Capacitance	$C_{OSS}$			133		
Reverse Transfer Capacitance	$C_{RSS}$			13		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5/18 V, V_{DS} = 520 V,$ $I_D = 20 A$ (Note 5)		74		nC
Gate-to-Source Charge	$Q_{GS}$			20		
Gate-to-Drain Charge	$Q_{GD}$			23		
Gate-Resistance	$R_G$	$f = 1 MHz$		3.9		Ω

### SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/18 V, V_{DS} = 400 V,$ $I_D = 20 A, R_G = 2.2 \Omega,$ Inductive Load (Note 5)		11		ns
Rise Time	$t_r$			14		
Turn-Off Delay Time	$t_{d(OFF)}$			24		
Fall Time	$t_f$			11		
Turn-On Switching Loss	$E_{ON}$			45		μJ
Turn-Off Switching Loss	$E_{OFF}$			18		
Total Switching Loss	$E_{TOT}$			63		

### SOURCE-DRAIN DIODE CHARACTERISTICS

Continuous Source-Drain Diode Forward Current	$I_{SD}$	$V_{GS} = -5 V, T_J = 25^\circ C$ (Note 5)			46	A
Pulsed Source-Drain Diode Forward Current (Note 2)	$I_{SDM}$	$V_{GS} = -5 V, T_J = 25^\circ C$ (Note 5)			115	A
Forward Diode Voltage	$V_{SD}$	$V_{GS} = -5 V, I_{SD} = 20 A, T_J = 25^\circ C$		4.3		V

# NTBL060N065SC1

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### SOURCE-DRAIN DIODE CHARACTERISTICS

Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = -5/18 V, I <sub>SD</sub> = 20 A, dI <sub>S</sub> /dt = 1000 A/μs (Note 5)		17.7		ns
Reverse Recovery Charge	Q <sub>RR</sub>		90.6		nC	
Reverse Recovery Energy	E <sub>REC</sub>		8.7		μJ	
Peak Reverse Recovery Current	I <sub>RRM</sub>		10.2		A	
Charge time	T <sub>a</sub>		9.8		ns	
Discharge time	T <sub>b</sub>		7.8		ns	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Defined by design, not subject to production test.

TYPICAL CHARACTERISTICS

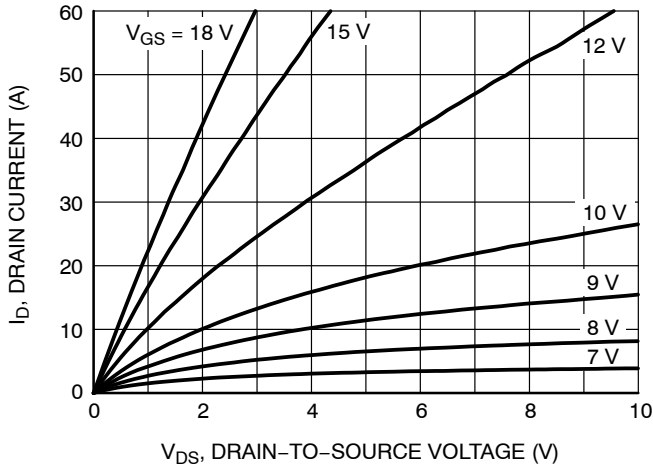


Figure 1. On-Region Characteristics

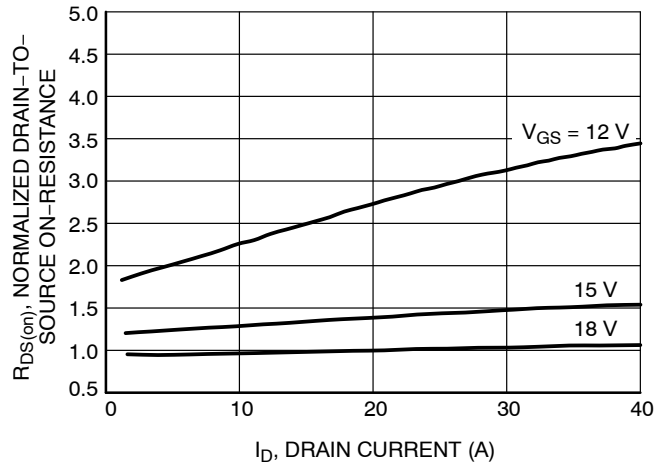


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

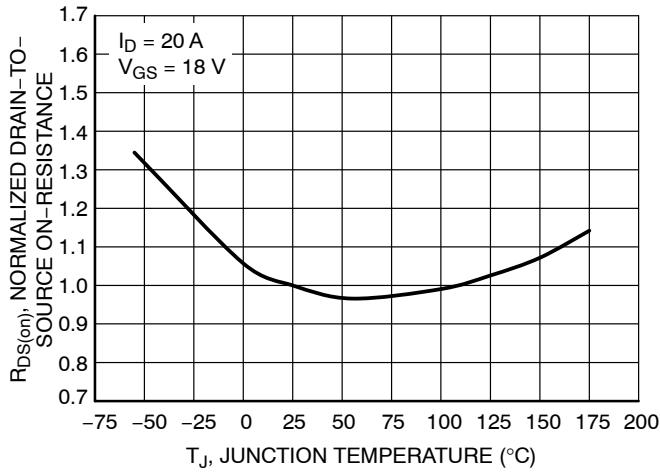


Figure 3. On-Resistance Variation with Temperature

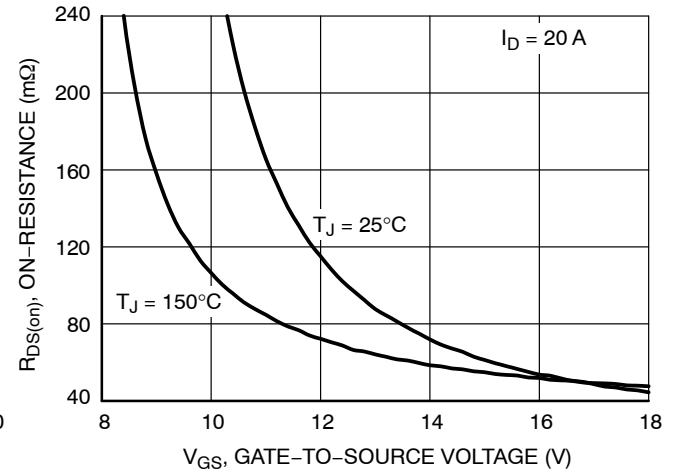


Figure 4. On-Resistance vs. Gate-to-Source Voltage

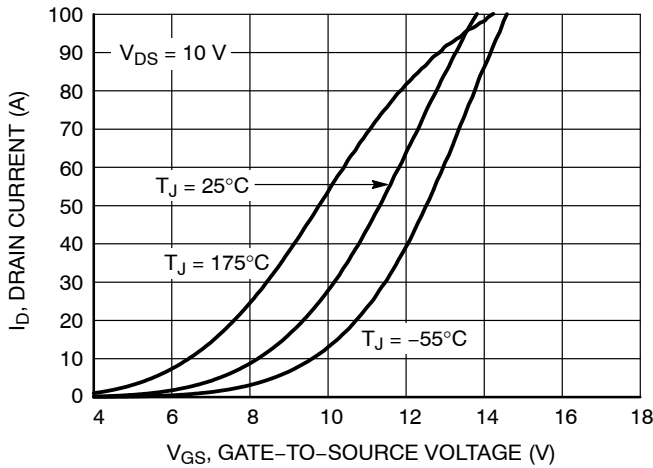


Figure 5. Transfer Characteristics

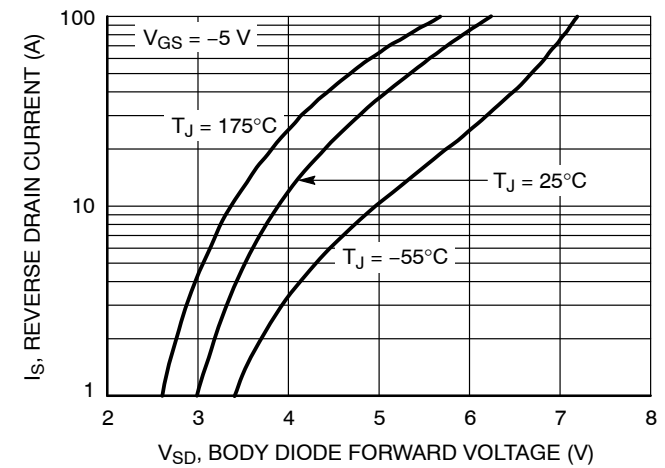


Figure 6. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

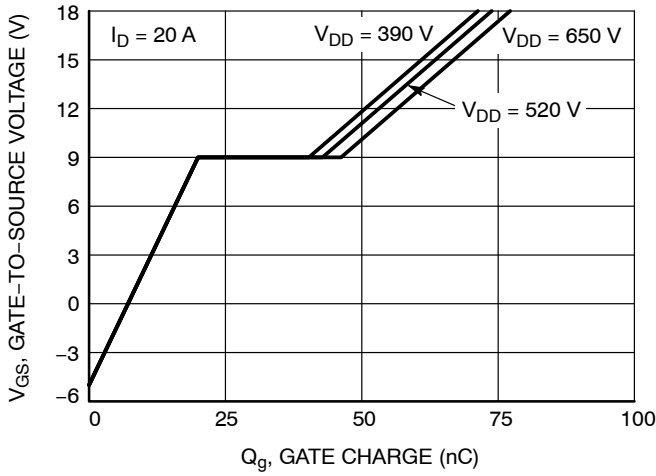


Figure 7. Gate-to-Source Voltage vs. Total Charge

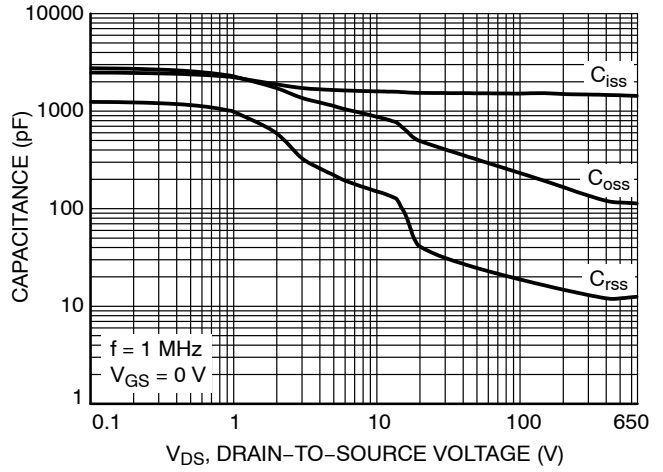


Figure 8. Capacitance vs. Drain-to-Source Voltage

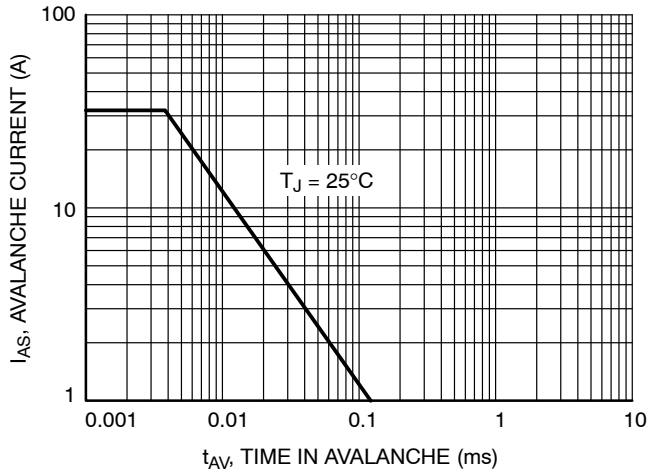


Figure 9. Unclamped Inductive Switching Capability

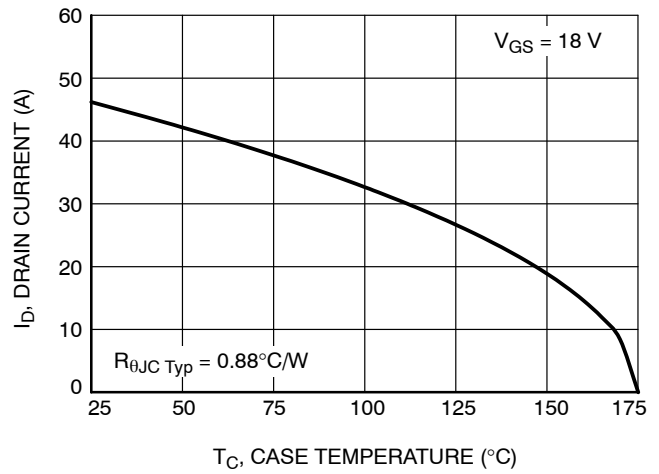


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

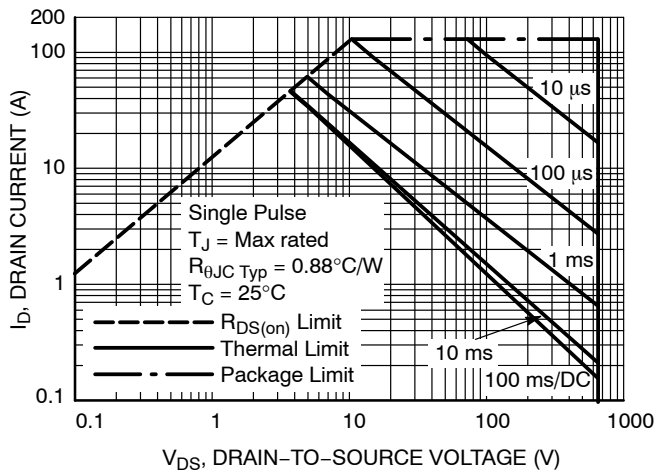


Figure 11. Safe Operating Area

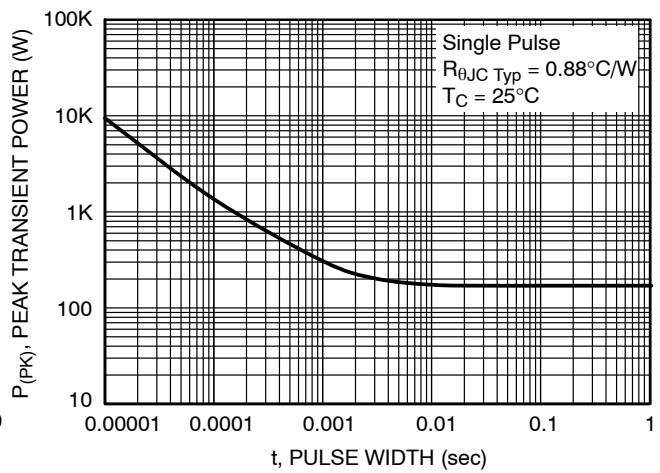


Figure 12. Single Pulse Maximum Power Dissipation

# NTBL060N065SC1

## TYPICAL CHARACTERISTICS

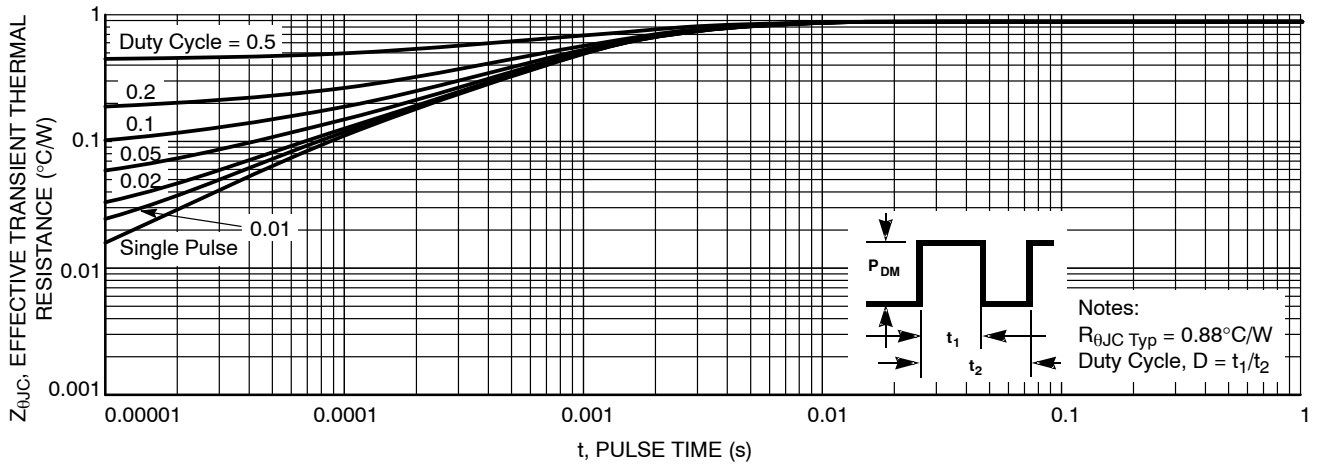


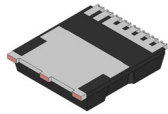
Figure 13. Junction-to-Case Transient Thermal Response

### DEVICE ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTBL060N065SC1	H-PSOF8L	2000 / Tape & Reel

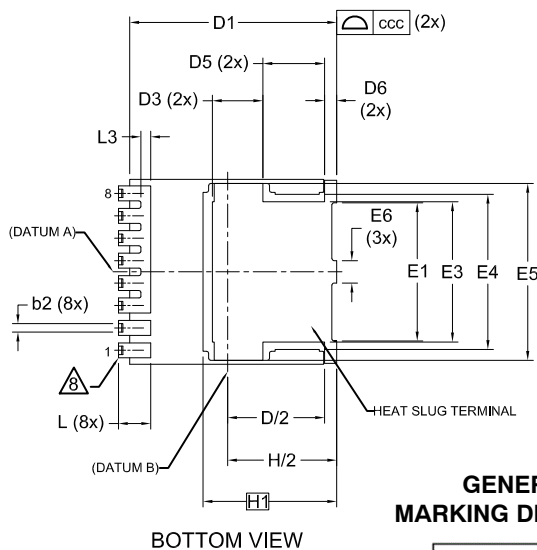
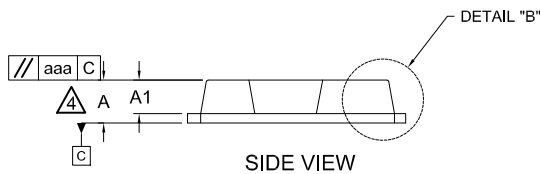
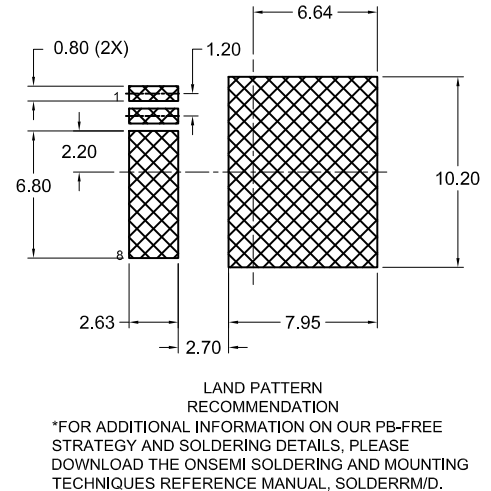
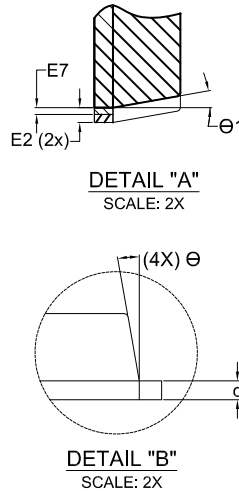
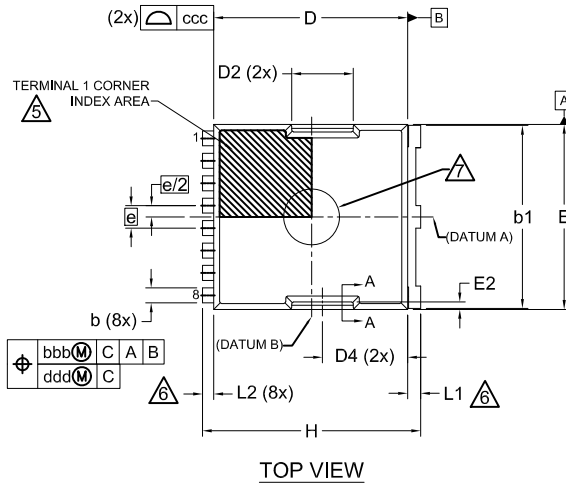
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



## H-PSOF8L 9.90x10.38x2.30, 1.20P CASE 100DC ISSUE B

DATE 30 APR 2024



### GENERIC MARKING DIAGRAM\*



XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Assembly Lot Code

#### NOTES:

1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE B.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
3. "e" REPRESENTS THE TERMINAL PITCH.
4. THIS DIMENSION INCLUDES ENCAPSULATION THICKNESS "A1", AND PACKAGE BODY THICKNESS, BUT DOES NOT INCLUDE ATTACHED FEATURES, e.g., EXTERNAL OR CHIP CAPACITORS. AN INTEGRAL HEATSLUG IS NOT CONSIDERED AS ATTACHED FEATURE.
5. A VISUAL INDEX FEATURE MUST BE LOCATED WITHIN THE HATCHED AREA.
6. DIMENSIONS b1, L1, L2 APPLY TO PLATED TERMINALS.
7. THE LOCATION AND SIZE OF EJECTOR MARKS ARE OPTIONAL.
8. THE LOCATION AND NUMBER OF FUSED LEADS ARE OPTIONAL.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.35	0.45	0.55
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D/2	5.09	5.19	5.29
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	2.60	2.70	2.80
D4	4.45	4.55	4.65
D5	3.20	3.30	3.40
D6	0.55	0.65	0.75
E	9.80	9.90	10.00
E1	7.30	7.40	7.50
E2	0.30	0.40	0.50
E3	7.40	7.50	7.60
E4	8.20	8.30	8.40

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E5	9.36	9.46	9.47
E6	1.10	1.20	1.30
E7	0.15	0.18	0.21
e	1.20 BSC		
e/2	0.60 BSC		
H	11.58	11.68	11.78
H/2	5.74	5.84	5.94
H1	7.15 BSC		
L	1.63	1.73	1.83
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.43	0.53	0.63
θ	10° REF		
θ1	10° REF		
aaa	0.20		
bbb	0.25		
ccc	0.20		
ddd	0.20		
eee	0.10		

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "μ", may or may not be present. Some products may not follow the Generic Marking.

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